Amdt. Dated: December 9, 2003

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Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

semiconductor device 1 Claim 1 (Original): Α comprising a substrate having an insulating layer formed on 2 a surface thereof, a semiconductor material layer located 3 on a surface of the insulating layer, a trench that extends 4 from a surface of the semiconductor material layer through 5 the insulating layer and into the substrate, an insulating 6 liner located on the side walls and the base of the trench, 7 8 and an in-fill of thermally-conductive material within the 9 insulating liner, wherein the insulating liner, the in-fill 10 material and the distance over which the trench extends into the substrate are such as to promote flow of heat from 11 the semiconductor material layer to the substrate, the 12 13 liner completely surrounding the in-fill insulating 14 least where the trench extends into the material at substrate, and said distance is at least 1 µm. 15

- 1 Claim 2 (Original): A semiconductor device is 2 claimed in claim 1, wherein said distance lies within the
- 3 range of from 1 µm to 5 µm.

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- 1 Claim 3 (Original): A semiconductor device is
- 2 claimed in claim 2, wherein said distance lies within the
- 3 range of from 3 μ m to 5 μ m.
- 1 Claim 4 (Original): A semiconductor device as
- 2 claimed in any one of claims 1 to 3, wherein there are two
- 3 trenches, each of which has the features defined in
- 4 claim 1, and wherein an active device is formed in the
- 5 semiconductor material layer between the two trenches.
- 1 Claim 5 (Currently amended): A semiconductor device
- 2 as claimed in any one of claims 1 to [[4]] 3, wherein there
- 3 are a plurality of trenches, each of which has the features
- 4 defined in claim 1, and wherein a respective active device
- 5 is formed in the semiconductor material layer between each
- 6 pair of adjacent trenches.
- 1 Claim 6 (Currently amended): A semiconductor device
- 2 as claimed in any one of claims 1 to [[5]] 3, wherein the
- 3 semiconductor material layer is a silicon layer.
- 1 Claim 7 (Original): A semiconductor device as
- 2 claimed in claim 6, wherein the silicon layer is of single
- 3 crystal formation.

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- 1 Claim 8 (Currently amended): A semiconductor device
- 2 as claimed in any one of claims 1 to [[7]] 3, wherein the
- 3 substrate is a silicon substrate.
- 1 Claim 9 (Currently amended): A semiconductor device
- 2 as claimed in any one of claims 1 to [[8]] 3, wherein the
- 3 insulating layer is a silicon oxide layer.
- 1 Claim 10 (Currently amended): A semiconductor device
- 2 as claimed in any one of claims 1 to [[9]] 3, wherein the
- 3 or each liner is constituted by an outer layer of silicon
- 4 oxide and an inner layer of silicon nitride.
- 1 Claim 11 (Currently amended): A semiconductor device
- 2 as claimed in claim 10, wherein the or each outer silicon
- 3 oxide layer has a thickness of substantially 1,000 [[A°]]
- 4 A, and the or each inner silicon nitride layer has a
- 5 thickness of substantially 300 [[A°]] $\underline{\mathring{A}}$.
- 1 Claim 12 (Currently amended): A semiconductor device
- 2 as claimed in any one of claims 1 to [[11]] 3, wherein the
- 3 in-fill material is polysilicon.
- 1 Claim 13 (Currently amended): A semiconductor device
- 2 as claimed in claim 12, wherein the width of the or each
- 3 trench is substantially 0.8 μm.

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- 1 Claim 14 (Currently amended): A semiconductor device
- 2 as claimed in any one of claims 1 to 13, wherein the
- 3 thickness of the or each liner is at least an order of
- 4 magnitude less than the thickness of the insulating layer.